

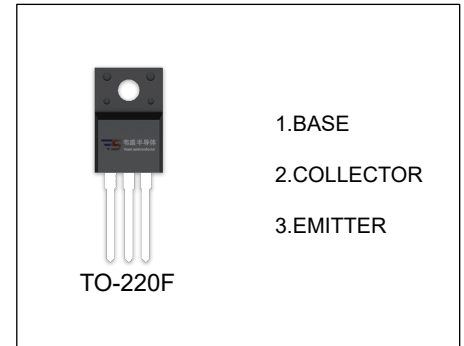
## 3DA5371 TRANSISTOR (NPN)

### FEATURES

- Breakdown Voltage High
- Reverse Cut-off Current Small
- Saturation Voltage Low
- Power dissipation

$$P_{CM} : 1.5W (T_a=25.)$$

$$25 W (T_c=25.)$$



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	1.5	A
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	180			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	160			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =180V, I <sub>E</sub> =0			10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =6V, I <sub>C</sub> =0			10	μA
DC current gain	h <sub>FE</sub> *	V <sub>CE</sub> =5V, I <sub>C</sub> =200mA	60		240	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	50			MHz

\*Pulse test: t<sub>p</sub>≤300μS, δ≤0.02.

### CLASSIFICATION OF h<sub>FE</sub>

Rank	O	R
Range	60-140	100-240